

Rajab Yahyazadeh

List of Publications by Year in descending order

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18
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docs citations

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36
citing authors

#	ARTICLE	IF	CITATIONS
1	Effect of hydrostatic pressure on the photocurrent density of InGaN/GaN multiple quantum well solar cells. Indian Journal of Physics, 2022, 96, 2815-2826.	1.8	4
2	Effect of Hydrostatic Pressure and Temperature on Quantum Confinement of AlGaIn/GaN HEMTs. Journal of Science and Technology, 2021, 13, .	0.2	2
3	Optical gain of AlGaIn/GaN multiquantum well laser diode influenced by hydrostatic pressure. Journal of Nanophotonics, 2021, 15, .	1.0	2
4	Effect of hydrostatic pressure on the radiative current density of InGaIn/GaN multiple quantum well light emitting diodes. Optical and Quantum Electronics, 2021, 53, 1.	3.3	2
5	Numerical modeling of electronic and electrical characteristics of InGaIn/GaN multiple quantum well solar cells. Journal of Photonics for Energy, 2020, 10, .	1.3	5
6	Numerical Optimization for Source-Drain Channel Resistance of AlGaIn/GaN HEMTs. Journal of Science and Technology, 2019, 11, .	0.2	1
7	Stability analysis of FGM microgripper subjected to nonlinear electrostatic and temperature variation loadings. Science and Engineering of Composite Materials, 2016, 23, 199-207.	1.4	13
8	Effect of Temperature on the Total Mobility of AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2014, 60, 1051-1055.	0.5	1
9	Effect of AlGaIn Barrier Thickness on the Transconductance of AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2014, 60, 57-61.	0.5	0
10	Effect of Temperature on the Cut off Frequency of AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2014, 60, 1021-1026.	0.5	0
11	Effect of temperature on the transconductance of AlGaIn/GaN high electron mobility transistors (HEMT). International Journal of Academic Research, 2013, 5, 78-86.	0.1	2
12	Effect of AlGaIn Barrier Thickness on the Cut Off Frequency of AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2012, 44, 165-172.	0.5	0
13	Effect of AlGaIn barrier thickness on the cut off frequency of AlGaIn/GaN High electron mobility transistors. International Journal of Academic Research, 2012, 4, 72-78.	0.1	0
14	Analytical-Numerical Model for the Total Mobility of AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2012, 44, 49-55.	0.5	0
15	Effect of AlGaIn Barrier Thickness on the Noise of AlGaIn/GaN High Electron Mobility Transistors. ECS Transactions, 2011, 34, 67-73.	0.5	0
16	Effect of temperature on the electronic current of two dimensional quantum well in AlGaIn/GaN high electron mobility transistors (HEMT). , 2010, , .		0
17	The effect of depletion layer on the cut off frequency of AlGaIn/GaN high electron mobility transistors. , 2010, , .		1
18	The effects of depletion layer on negative differential conductivity in AlGaIn/GaN high electron mobility transistor. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 33, 77-82.	2.7	9